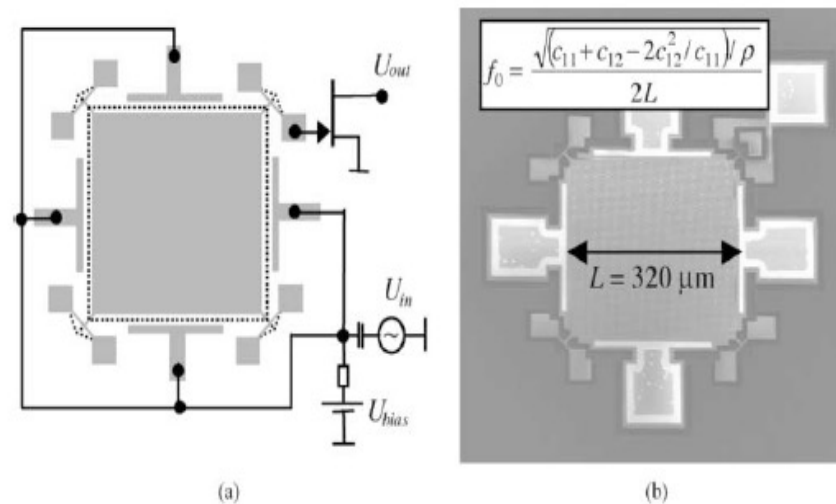


In-plane bulk-mode resonators (Lamé, breathing...)

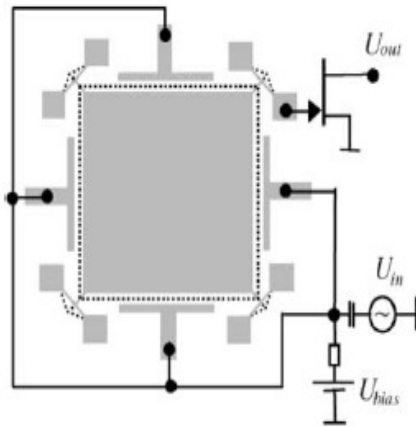


Here $h=10\ \mu\text{m}$ thick

Fig. 1. Square-extensional microresonator ($f_0 = 13.1\ \text{MHz}$ and $Q = 130\,000$). (a) Schematic of the resonator showing the vibration mode in the expanded shape and biasing and driving setup. (b) SEM image of the resonator.

V. Kaajakari et al., « Square-Extensional Mode Single-Crystal Silicon Micromechanical Resonator for Low-Phase-Noise Oscillator Applications », IEEE ELECTRON DEVICE LETTERS, VOL. 25, NO. 4, 2004

Bulk mode: large mass, high Q, can make as thick as technology allows



$320 \times 320 \times 10 \text{ } \mu\text{m}^3$

For this mode, the spring constant is:

$$k = \pi^2 Y_{2D} h$$

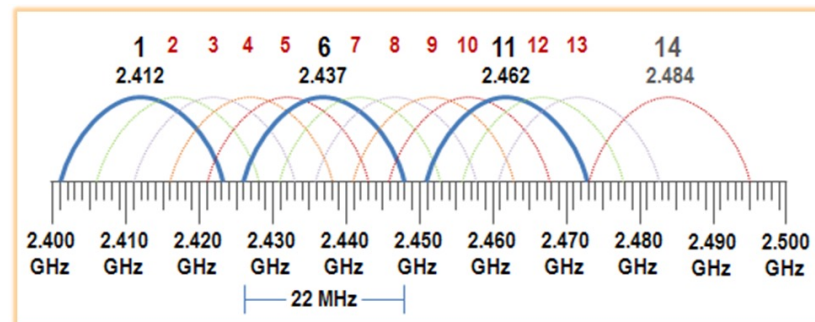
With $Y_{2D} = 181 \text{ GPa}$

1. Compute f_{res} for given dimensions
2. How does f_{res} depend on h ?

$$Y_{2D} = c_{11} + c_{12} - 2 \frac{c_{12}^2}{c_{11}} = 181 \text{ GPa}$$

Frequency

- If we allow max 0.1% change in frequency, how much change in L can be tolerated?
- Is this feasible? (= how well can we control L?)



Motion due to ES force

- Compute k . how does this compare to spring constants you usually see in MEMS? Stiffer? Softer?
- compute the electrostatic force from the bias voltage only
 - Gap is $0.75\text{ }\mu\text{m}$,
 - electrode length is $290\text{ }\mu\text{m}$,
 - Bias voltage = 100 V .
- compute the electrostatic force from the AC voltage
 - $Q=6200$
 - $V_{ac} = 1\text{ V}$
- Compute the static displacement due to the bias voltage . Comments?

Thermal vs. mechanical energy

- At resonance, we have $x_{\text{vib}} = 1.5 \text{ nm}$
- Compare thermal energy and mechanical energy. Your comments?
- E_{mech} : how does it scale with h ? With V ?
- How low would the bias voltage have to be to have: $E_{\text{mech}} = 100 \times E_{\text{thermal}}$?